

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application of: Shunichi SATO, Akihiro ITOH and Naoto JIKUTANI

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1185 Avenue of the Americas
New York, N.Y. 10036
(212) 278-0400

Mail Stop PCT

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INFORMATION DISCLOSURE STATEMENT

Pursuant to the applicant's duty of disclosure, the information listed in the attached Form PTO-1449 is brought to the attention of the Examiner.

It is respectfully requested that the information cited in annexed Form PTO-1449 be considered by the Examiner in connection with the above-identified patent application, filed concurrently herewith, and that such art be made of record in said application.

The subject application is a U.S. national phase application under 35 U.S.C. 371 of International Application No. PCT/JP2005/010520. Several of the items listed on the annexed Form PTO-1449 was cited in the International Search Report and/or Written Opinion in connection with International Application No. PCT/JP2005/010520. Copies of the International Search Report and/or Written Opinion are submitted concurrently herewith.

The citation of the listed items is not a representation that they constitute a complete or exhaustive listing of the relevant art or that these items are prior art. The items listed are

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submitted in good faith, but are not intended to substitute for the Examiner's search. It is hoped, however, that in addition to apprising the Examiner of the particular items, they will assist in identifying fields of search and in making as full and complete a search as possible.

The filing of this Information Disclosure Statement is not an admission that the information cited herein is, or is considered to be, material to patentability as defined in 37 C.F.R. §1.56(b).


According to the August 5, 2003 OG Notice published by the Patent and Trademark Office, the Office has waived the requirement under 37 C.F.R. §1.98(a)(2)(i) for submitting a copy of each cited U.S. patent and each cited U.S. patent application publication for all U.S. national patent applications filed after June 30, 2003 and for all international application that have entered the national stage under 35 U.S.C. §371 after June 30, 2003.

Accordingly, copies are submitted herewith for only references listed on the annexed Form PTO-1449 that are not a U.S. patent or U.S. patent application publication.

The Office is hereby authorized to charge any fees which may be required for consideration of this Information Disclosure Statement and to credit any overpayment to our Deposit Account No. 03-3125.

Respectfully submitted,

Date: February 7, 2006


Paul Teng, Reg. No. 40,837
Attorney for Applicant
Cooper & Dunham LLP
(212) 278-0400

Form PTO-1449

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(Use several sheets if necessary)Applicant:
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Group Art Unit:

U.S. PATENT DOCUMENTS

Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate
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	6 2 3 3 2 6 4	5-15-2001	Sato			
	20 02 /0 10 18 99 A1	8-1-2002	Yokouchi et al.			
	20 03 /0 04 38 75 A1	3-6-2003	Gen-Ei et al.			
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						Yes	No
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	Nobuhiko NISHIYAMA et al. (December 1998) "Single-Transverse Mode and Stable-Polarization Operation Under High-Speed Modulation of InGaAs-GaAs Vertical-Cavity Surface-Emitting Laser Grown on GaAs (311) B Substrate", IEEE Photonics Technology Letters, Vol. 10, No. 12, pages 1676-1678.
	N. TANSU et al. (June 2000) "Low-Temperature Sensitive, Compressively Strained InGaAsP Active (= 0.78-0.85 m) Region Diode Lasers", IEEE Photonics Technology Letter, Vol. 12, No. 6, pages 603-605.

EXAMINER

DATE CONSIDERED

*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609: Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.